

SONY**1T33/1T33A****Silicon Variable Capacitance Diode****Description**

The 1T33/1T33A is a variable capacitance diode designed for use in electric tuning for CATV tuner which make their packages more compact so as to match tuner miniturization easily, keeping excellent characteristics of former 1T31 type.

Features

- Compact package
- Low serial resistance $0.8\ \Omega$ Typ. ($f = 470\ \text{MHz}$)
- Large capacitance ratio 10 Min. (C_2/C_1)
- Small leakage current 10 nA Max. ($V_R = 28\text{V}$)
- 1T33(A)-T7, 1T33(A)-T8 is for taping.

Structure

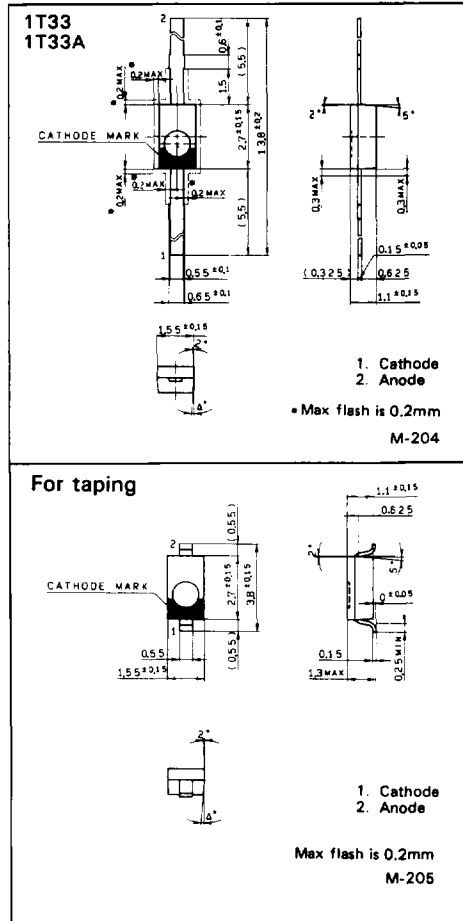
Silicon epitaxial planar type diode

Application

Electric tuning for TV or CATV

Package Outline

Unit: mm

**Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)**

• Reverse voltage	V_R	30	V
• Peak reverse voltage	V_{RM}	35	V ($R_L \geq 10\ \text{k}\Omega$)
• Operating temperature	T_{opr}	85	$^\circ\text{C}$
• Storage temperature	T_{stg}	-30 to +120	$^\circ\text{C}$

71019-T0

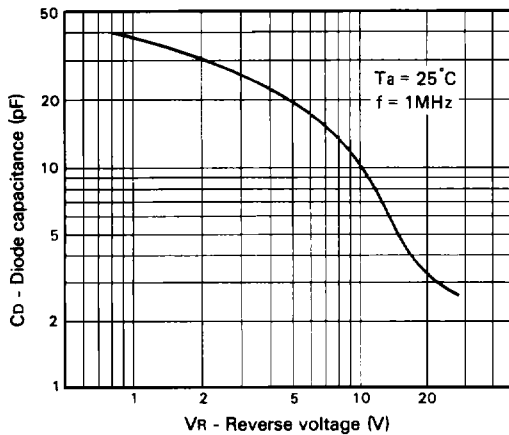
Electrical Characteristics

Ta = 25°C

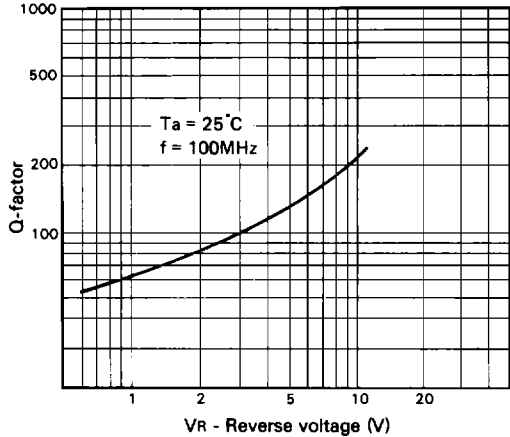
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse current	IR	VR = 28V			10	nA
Diode capacitance	C2	VR = 2V, f = 1 MHz	27.19		32.03	pF
	C25	VR = 25V, f = 1 MHz	2.71		3.04	pF
Serial resistance	rs	CD = 14pF, f = 470 MHz		0.7	0.8	Ω
Maximum-capacitance deviation in the same ranking*	ΔC	VR = 2 to 25V, f = 1 MHz			3 (1T33) 2 (1T33A)	%

*Note) Applied only to tuning.

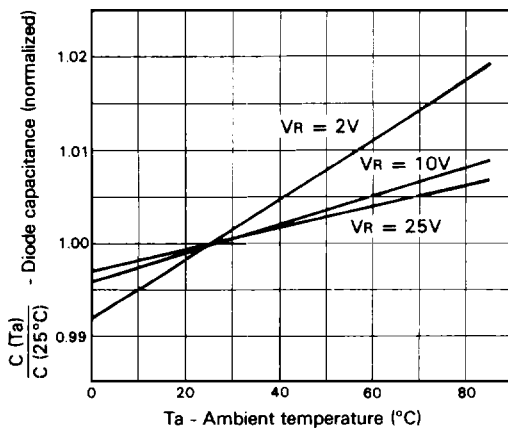
Diode capacitance vs. Reverse voltage



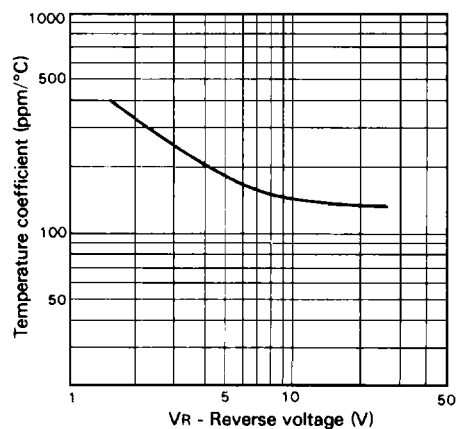
Q-factor vs. Reverse voltage



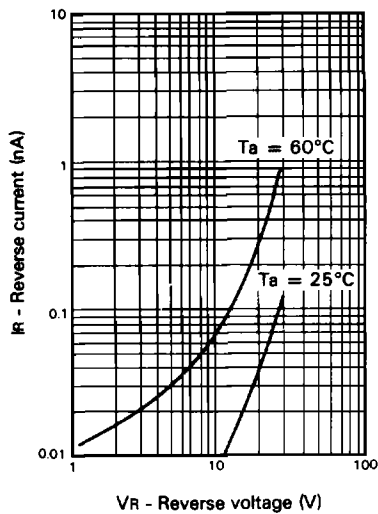
Diode capacitance vs. Ambient temperature



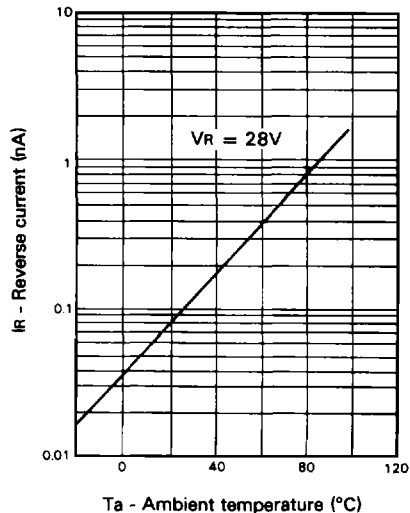
Temperature coefficient of the diode capacitance



Reverse current vs. Reverse voltage



Reverse current vs. Ambient temperature



Reverse breakdown voltage vs. Ambient temperature

